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Details

Product Status	Active
Core Processor	e200z0h
Core Size	32-Bit Single-Core
Speed	64MHz
Connectivity	CANbus, I ² C, LINbus, SCI, SPI
Peripherals	DMA, POR, PWM, WDT
Number of I/O	149
Program Memory Size	1MB (1M x 8)
Program Memory Type	FLASH
EEPROM Size	64K x 8
RAM Size	80K x 8
Voltage - Supply (Vcc/Vdd)	3V ~ 5.5V
Data Converters	A/D 29x10b, 5x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	176-LQFP
Supplier Device Package	176-LQFP (24x24)
Purchase URL	https://www.e-xfl.com/product-detail/nxp-semiconductors/spc5606bk0clu4

Figure 3 shows the MPC5606BK in the 144 LQFP package.

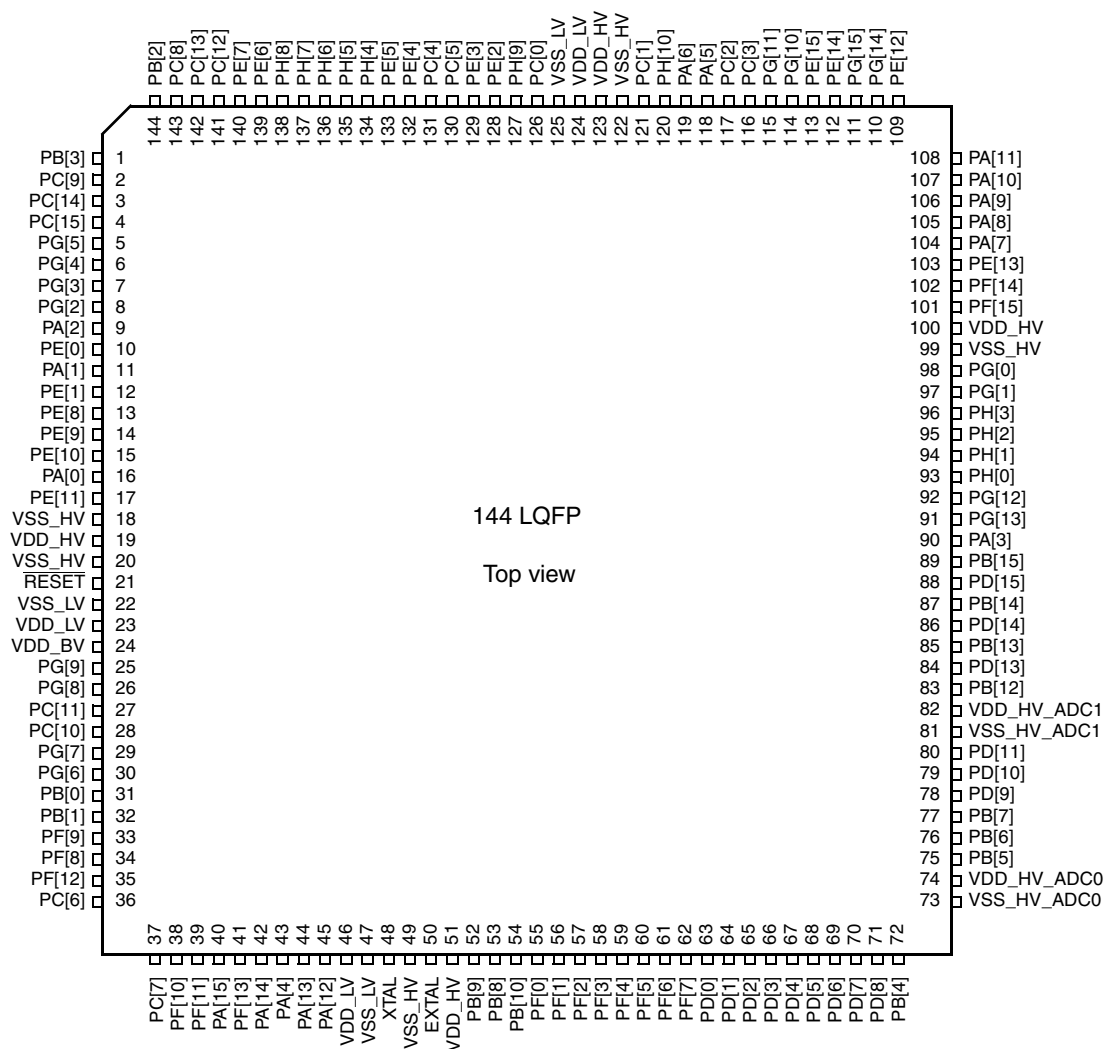


Figure 3. 144 LQFP pinout

Figure 4 shows the MPC5606BK in the 100 LQFP package.

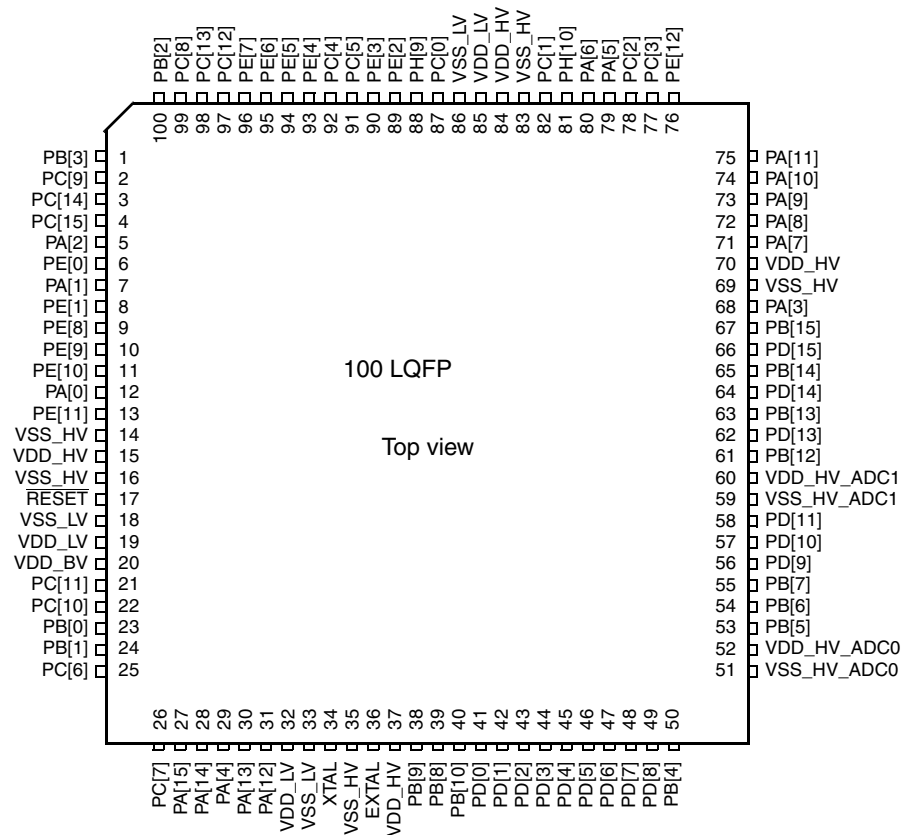


Figure 4. 100 LQFP pinout

2.2 Pin muxing

Table 2 defines the pin list and muxing for this device.

Each entry of Table 2 shows all the possible configurations for each pin, via the alternate functions. The default function assigned to each pin after reset is indicated by AF0.

Table 2. Functional port pins

Port pin	PCR register	Alternate function ¹	Function	Peripheral	I/O direction	Pad type ²	RESET config. ³	Pin number		
								100 LQFP	144 LQFP	176 LQFP
Port A										
PA[0]	PCR[0]	AF0 AF1 AF2 AF3 —	GPIO[0] E0UC[0] CLKOUT E0UC[13] WKUP[19] ⁴	SIUL eMIOS_0 MC_CGM eMIOS_0 WKUP	I/O I/O O I/O I	M	Tristate	12	16	24
PA[1]	PCR[1]	AF0 AF1 AF2 AF3 —	GPIO[1] E0UC[1] NMI ⁵ — WKUP[2] ⁴	SIUL eMIOS_0 WKUP — WKUP	I/O I/O I — I	S	Tristate	7	11	19
PA[2]	PCR[2]	AF0 AF1 AF2 AF3 —	GPIO[2] E0UC[2] — MA[2] WKUP[3] ⁴	SIUL eMIOS_0 — ADC_0 WKUP	I/O I/O — O I	S	Tristate	5	9	17
PA[3]	PCR[3]	AF0 AF1 AF2 AF3 — —	GPIO[3] E0UC[3] LIN5TX CS4_1 EIRQ[0] ADC1_S[0]	SIUL eMIOS_0 LINFlex_5 DSPI_1 SIUL ADC_1	I/O I/O O O I I	J	Tristate	68	90	114
PA[4]	PCR[4]	AF0 AF1 AF2 AF3 — —	GPIO[4] E0UC[4] — CS0_1 LIN5RX WKUP[9] ⁴	SIUL eMIOS_0 — DSPI_1 LINFlex_5 WKUP	I/O I/O — I/O I I	S	Tristate	29	43	51
PA[5]	PCR[5]	AF0 AF1 AF2 AF3	GPIO[5] E0UC[5] LIN4TX —	SIUL eMIOS_0 LINFlex_4 —	I/O I/O O —	M	Tristate	79	118	146
PA[6]	PCR[6]	AF0 AF1 AF2 AF3 — —	GPIO[6] E0UC[6] — CS1_1 EIRQ[1] LIN4RX	SIUL eMIOS_0 — DSPI_1 SIUL LINFlex_4	I/O I/O — O I I	S	Tristate	80	119	147

Table 2. Functional port pins (continued)

Port pin	PCR register	Alternate function ¹	Function	Peripheral	I/O direction	Pad type ²	RESET config. ³	Pin number		
								100 LQFP	144 LQFP	176 LQFP
PA[7]	PCR[7]	AF0 AF1 AF2 AF3 — —	GPIO[7] E0UC[7] LIN3TX — EIRQ[2] ADC1_S[1]	SIUL eMIOS_0 LINFlex_3 — SIUL ADC_1	I/O I/O O — I I	J	Tristate	71	104	128
PA[8]	PCR[8]	AF0 AF1 AF2 AF3 — — N/A ⁶ —	GPIO[8] E0UC[8] E0UC[14] — EIRQ[3] ABS[0] LIN3RX	SIUL eMIOS_0 eMIOS_0 — SIUL BAM LINFlex_3	I/O I/O I/O — I I I	S	Input, weak pull-up	72	105	129
PA[9]	PCR[9]	AF0 AF1 AF2 AF3 N/A ⁶	GPIO[9] E0UC[9] — CS2_1 FAB	SIUL eMIOS_0 — DSPI_1 BAM	I/O I/O — O I	S	Pull-down	73	106	130
PA[10]	PCR[10]	AF0 AF1 AF2 AF3 —	GPIO[10] E0UC[10] SDA LIN2TX ADC1_S[2]	SIUL eMIOS_0 I ² C_0 LINFlex_2 ADC_1	I/O I/O I/O O I	J	Tristate	74	107	131
PA[11]	PCR[11]	AF0 AF1 AF2 AF3 — — —	GPIO[11] E0UC[11] SCL — EIRQ[16] LIN2RX ADC1_S[3]	SIUL eMIOS_0 I ² C_0 — SIUL LINFlex_2 ADC_1	I/O I/O I/O — I I I	J	Tristate	75	108	132
PA[12]	PCR[12]	AF0 AF1 AF2 AF3 — —	GPIO[12] — E0UC[28] CS3_1 EIRQ[17] SIN_0	SIUL — eMIOS_0 DSPI_1 SIUL DSPI_0	I/O — I/O O I I	S	Tristate	31	45	53
PA[13]	PCR[13]	AF0 AF1 AF2 AF3	GPIO[13] SOUT_0 E0UC[29] —	SIUL DSPI_0 eMIOS_0 —	I/O O I/O —	M	Tristate	30	44	52
PA[14]	PCR[14]	AF0 AF1 AF2 AF3 —	GPIO[14] SCK_0 CS0_0 E0UC[0] EIRQ[4]	SIUL DSPI_0 DSPI_0 eMIOS_0 SIUL	I/O I/O I/O I/O I	M	Tristate	28	42	50

Table 2. Functional port pins (continued)

Port pin	PCR register	Alternate function ¹	Function	Peripheral	I/O direction	Pad type ²	RESET config. ³	Pin number		
								100 LQFP	144 LQFP	176 LQFP
PA[15]	PCR[15]	AF0 AF1 AF2 AF3 —	GPIO[15] CS0_0 SCK_0 E0UC[1] WKUP[10] ⁴	SIUL DSPI_0 DSPI_0 eMIOS_0 WKUP	I/O I/O I/O I/O I	M	Tristate	27	40	48
Port B										
PB[0]	PCR[16]	AF0 AF1 AF2 AF3	GPIO[16] CAN0TX E0UC[30] LIN0TX	SIUL FlexCAN_0 eMIOS_0 LINFlex_0	I/O O I/O O	M	Tristate	23	31	39
PB[1]	PCR[17]	AF0 AF1 AF2 AF3 — — —	GPIO[17] — E0UC[31] — WKUP[4] ⁴ CAN0RX LIN0RX	SIUL — eMIOS_0 — WKUP FlexCAN_0 LINFlex_0	I/O — I/O — I I I	S	Tristate	24	32	40
PB[2]	PCR[18]	AF0 AF1 AF2 AF3	GPIO[18] LIN0TX SDA E0UC[30]	SIUL LINFlex_0 I ² C_0 eMIOS_0	I/O O I/O I/O	M	Tristate	100	144	176
PB[3]	PCR[19]	AF0 AF1 AF2 AF3 — —	GPIO[19] E0UC[31] SCL — WKUP[11] ⁴ LIN0RX	SIUL eMIOS_0 I ² C_0 — WKUP LINFlex_0	I/O I/O I/O — I I	S	Tristate	1	1	1
PB[4]	PCR[20]	AF0 AF1 AF2 AF3 — — —	— — — — ADC0_P[0] ADC1_P[0] GPIO[20]	— — — — ADC_0 ADC_1 SIUL	— — — — I I I	I	Tristate	50	72	88
PB[5]	PCR[21]	AF0 AF1 AF2 AF3 — — —	— — — — ADC0_P[1] ADC1_P[1] GPIO[21]	— — — — ADC_0 ADC_1 SIUL	— — — — I I I	I	Tristate	53	75	91

Table 2. Functional port pins (continued)

Port pin	PCR register	Alternate function ¹	Function	Peripheral	I/O direction	Pad type ²	RESET config. ³	Pin number		
								100 LQFP	144 LQFP	176 LQFP
PB[6]	PCR[22]	AF0	—	—	—	I	Tristate	54	76	92
		AF1	—	—	—					
		AF2	—	—	—					
		AF3	—	—	—					
		—	ADC0_P[2]	ADC_0	I					
		—	ADC1_P[2]	ADC_1	I					
		—	GPIO[22]	SIUL	I					
PB[7]	PCR[23]	AF0	—	—	—	I	Tristate	55	77	93
		AF1	—	—	—					
		AF2	—	—	—					
		AF3	—	—	—					
		—	ADC0_P[3]	ADC_0	I					
		—	ADC1_P[3]	ADC_1	I					
		—	GPIO[23]	SIUL	I					
PB[8]	PCR[24]	AF0	GPIO[24]	SIUL	I	I	—	39	53	61
		AF1	—	—	—					
		AF2	—	—	—					
		AF3	—	—	—					
		—	OSC32K_XTAL ⁷	OSC32K	—					
		—	WKUP[25]	WKUP	I					
		—	ADC0_S[0]	ADC_0	I					
PB[9]	PCR[25]	—	ADC1_S[4]	ADC_1	I					
		AF0	GPIO[25]	SIUL	I	I	—	38	52	60
		AF1	—	—	—					
		AF2	—	—	—					
		AF3	—	—	—					
		—	OSC32K_EXTAL ⁷	OSC32K	—					
		—	WKUP[26]	WKUP	I					
PB[10]	PCR[26]	—	ADC0_S[1]	ADC_0	I					
		—	ADC1_S[5]	ADC_1	I					
		AF0	GPIO[26]	SIUL	I/O	J	Tristate	40	54	62
		AF1	—	—	—					
		AF2	—	—	—					
		AF3	—	—	—					
		—	WKUP[8] ⁴	WKUP	I					
PB[11]	PCR[27]	—	ADC0_S[2]	ADC_0	I					
		—	ADC1_S[6]	ADC_1	I					
		AF0	GPIO[27]	SIUL	I/O	J	Tristate	—	—	97
		AF1	E0UC[3]	eMIOS_0	I/O					
		AF2	—	—	—					
		AF3	CS0_0	DSPI_0	I/O					
		—	ADC0_S[3]	ADC_0	I					
PB[12]	PCR[28]	AF0	GPIO[28]	SIUL	I/O	J	Tristate	61	83	101
		AF1	E0UC[4]	eMIOS_0	I/O					
		AF2	—	—	—					
		AF3	CS1_0	DSPI_0	O					
		—	ADC0_X[0]	ADC_0	I					
		—	—	—	—					
		—	—	—	—					

Table 2. Functional port pins (continued)

Port pin	PCR register	Alternate function ¹	Function	Peripheral	I/O direction	Pad type ²	RESET config. ³	Pin number		
								100 LQFP	144 LQFP	176 LQFP
PC[14]	PCR[46]	AF0 AF1 AF2 AF3 —	GPIO[46] E0UC[14] SCK_2 — EIRQ[8]	SIUL eMIOS_0 DSPI_2 — SIUL	I/O I/O I/O — I	S	Tristate	3	3	3
PC[15]	PCR[47]	AF0 AF1 AF2 AF3 —	GPIO[47] E0UC[15] CS0_2 — EIRQ[20]	SIUL eMIOS_0 DSPI_2 — SIUL	I/O I/O I/O — I	M	Tristate	4	4	4
Port D										
PD[0]	PCR[48]	AF0 AF1 AF2 AF3 — — —	GPIO[48] — — — — WKUP[27] ADC0_P[4] ADC1_P[4]	SIUL — — — — WKUP ADC_0 ADC_1	I — — — — I I I	I	Tristate	41	63	77
PD[1]	PCR[49]	AF0 AF1 AF2 AF3 — — —	GPIO[49] — — — — WKUP[28] ADC0_P[5] ADC1_P[5]	SIUL — — — — WKUP ADC_0 ADC_1	I — — — — I I I	I	Tristate	42	64	78
PD[2]	PCR[50]	AF0 AF1 AF2 AF3 — —	GPIO[50] — — — — ADC0_P[6] ADC1_P[6]	SIUL — — — — ADC_0 ADC_1	I — — — — I I	I	Tristate	43	65	79
PD[3]	PCR[51]	AF0 AF1 AF2 AF3 — —	GPIO[51] — — — — ADC0_P[7] ADC1_P[7]	SIUL — — — — ADC_0 ADC_1	I — — — — I I	I	Tristate	44	66	80
PD[4]	PCR[52]	AF0 AF1 AF2 AF3 — —	GPIO[52] — — — — ADC0_P[8] ADC1_P[8]	SIUL — — — — ADC_0 ADC_1	I — — — — I I	I	Tristate	45	67	81

Table 2. Functional port pins (continued)

Port pin	PCR register	Alternate function ¹	Function	Peripheral	I/O direction	Pad type ²	RESET config. ³	Pin number		
								100 LQFP	144 LQFP	176 LQFP
PF[7]	PCR[87]	AF0	GPIO[87]	SIUL	I/O	J	Tristate	—	62	70
		AF1	—	—	—					
		AF2	CS2_1	DSPI_1	O					
		AF3	—	—	—					
		—	ADC0_S[15]	ADC_0	I					
PF[8]	PCR[88]	AF0	GPIO[88]	SIUL	I/O	M	Tristate	—	34	42
		AF1	CAN3TX	FlexCAN_3	O					
		AF2	CS4_0	DSPI_0	O					
		AF3	CAN2TX	FlexCAN_2	O					
PF[9]	PCR[89]	AF0	GPIO[89]	SIUL	I/O	S	Tristate	—	33	41
		AF1	E1UC[1]	eMIOS_1	I/O					
		AF2	CS5_0	DSPI_0	O					
		AF3	—	—	—					
		—	WKUP[22] ⁴	WKUP	I					
		—	CAN2RX	FlexCAN_2	I					
		—	CAN3RX	FlexCAN_3	I					
PF[10]	PCR[90]	AF0	GPIO[90]	SIUL	I/O	M	Tristate	—	38	46
		AF1	CS1_0	DSPI_0	O					
		AF2	LIN4TX	LINFlex_4	O					
		AF3	E1UC[2]	eMIOS_1	I/O					
PF[11]	PCR[91]	AF0	GPIO[91]	SIUL	I/O	S	Tristate	—	39	47
		AF1	CS2_0	DSPI_0	O					
		AF2	E1UC[3]	eMIOS_1	I/O					
		AF3	—	—	—					
		—	WKUP[15] ⁴	WKUP	I					
		—	LIN4RX	LINFlex_4	I					
PF[12]	PCR[92]	AF0	GPIO[92]	SIUL	I/O	M	Tristate	—	35	43
		AF1	E1UC[25]	eMIOS_1	I/O					
		AF2	LIN5TX	LINFlex_5	O					
		AF3	—	—	—					
PF[13]	PCR[93]	AF0	GPIO[93]	SIUL	I/O	S	Tristate	—	41	49
		AF1	E1UC[26]	eMIOS_1	I/O					
		AF2	—	—	—					
		AF3	—	—	—					
		—	WKUP[16] ⁴	WKUP	I					
		—	LIN5RX	LINFlex_5	I					
PF[14]	PCR[94]	AF0	GPIO[94]	SIUL	I/O	M	Tristate	—	102	126
		AF1	CAN4TX	FlexCAN_4	O					
		AF2	E1UC[27]	eMIOS_1	I/O					
		AF3	CAN1TX	FlexCAN_1	O					

Table 2. Functional port pins (continued)

Port pin	PCR register	Alternate function ¹	Function	Peripheral	I/O direction	Pad type ²	RESET config. ³	Pin number		
								100 LQFP	144 LQFP	176 LQFP
PG[7]	PCR[103]	AF0 AF1 AF2 AF3 — —	GPIO[103] E1UC[16] E1UC[30] — WKUP[20] ⁴ LIN6RX	SIUL eMIOS_1 eMIOS_1 — WKUP LINFlex_6	I/O I/O I/O — I I	S	Tristate	—	29	37
PG[8]	PCR[104]	AF0 AF1 AF2 AF3 —	GPIO[104] E1UC[17] LIN7TX CS0_2 EIRQ[15]	SIUL eMIOS_1 LINFlex_7 DSPI_2 SIUL	I/O I/O O I/O I	S	Tristate	—	26	34
PG[9]	PCR[105]	AF0 AF1 AF2 AF3 — —	GPIO[105] E1UC[18] — SCK_2 WKUP[21] ⁴ LIN7RX	SIUL eMIOS_1 — DSPI_2 WKUP LINFlex_7	I/O I/O — I/O I I	S	Tristate	—	25	33
PG[10]	PCR[106]	AF0 AF1 AF2 AF3 —	GPIO[106] E0UC[24] E1UC[31] — SIN_4	SIUL eMIOS_0 eMIOS_1 — DSPI_4	I/O I/O I/O — I	S	Tristate	—	114	138
PG[11]	PCR[107]	AF0 AF1 AF2 AF3	GPIO[107] E0UC[25] CS0_4 —	SIUL eMIOS_0 DSPI_4 —	I/O I/O O —	M	Tristate	—	115	139
PG[12]	PCR[108]	AF0 AF1 AF2 AF3	GPIO[108] E0UC[26] SOUT_4 —	SIUL eMIOS_0 DSPI_4 —	I/O I/O O —	M	Tristate	—	92	116
PG[13]	PCR[109]	AF0 AF1 AF2 AF3	GPIO[109] E0UC[27] SCK_4 —	SIUL eMIOS_0 DSPI_4 —	I/O I/O I/O —	M	Tristate	—	91	115
PG[14]	PCR[110]	AF0 AF1 AF2 AF3	GPIO[110] E1UC[0] — —	SIUL eMIOS_1 — —	I/O I/O — —	S	Tristate	—	110	134
PG[15]	PCR[111]	AF0 AF1 AF2 AF3 —	GPIO[111] E1UC[1] — — —	SIUL eMIOS_1 — — —	I/O I/O — — —	M	Tristate	—	111	135
Port H										

K is a constant for the particular part, which may be determined from [Equation 3](#) by measuring P_D (at equilibrium) for a known T_A . Using this value of K, the values of P_D and T_J may be obtained by solving equations [1](#) and [2](#) iteratively for any value of T_A .

3.6 I/O pad electrical characteristics

3.6.1 I/O pad types

The device provides four main I/O pad types depending on the associated alternate functions:

- Slow pads — are the most common pads, providing a good compromise between transition time and low electromagnetic emission.
- Medium pads — provide transition fast enough for the serial communication channels with controlled current to reduce electromagnetic emission.
- Fast pads — provide maximum speed. These are used for improved debugging capability.
- Input only pads — are associated with ADC channels and 32 kHz low power external crystal oscillator providing low input leakage.

Medium and Fast pads can use slow configuration to reduce electromagnetic emission, at the cost of reducing AC performance.

3.6.2 I/O input DC characteristics

[Table 12](#) provides input DC electrical characteristics as described in [Figure 5](#).

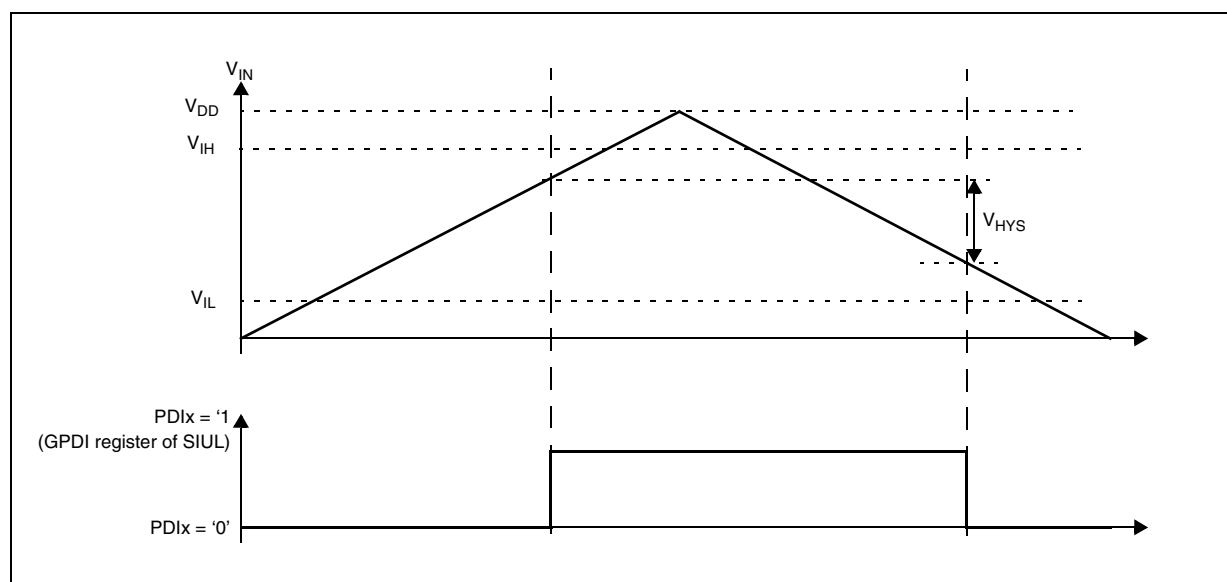


Figure 5. I/O input DC electrical characteristics definition

Table 21. Reset electrical characteristics (continued)

Symbol	C	Parameter	Conditions ¹	Value			Unit
				Min	Typ	Max	
V _{IL}	SR	P	Input low Level CMOS (Schmitt Trigger)	—	—	0.35V _{DD}	V
V _{HYS}	CC	C	Input hysteresis CMOS (Schmitt Trigger)	0.1V _{DD}	—	—	V
V _{OL}	CC	P	Output low level	Push Pull, I _{OL} = 2 mA, V _{DD} = 5.0 V ± 10%, PAD3V5V = 0 (recommended)	—	—	0.1V _{DD}
				Push Pull, I _{OL} = 1 mA, V _{DD} = 5.0 V ± 10%, PAD3V5V = 1 ²	—	—	0.1V _{DD}
				Push Pull, I _{OL} = 1 mA, V _{DD} = 3.3 V ± 10%, PAD3V5V = 1 (recommended)	—	—	0.5
T _{tr}	CC	D	Output transition time output pin ³ MEDIUM configuration	C _L = 25 pF, V _{DD} = 5.0 V ± 10%, PAD3V5V = 0	—	—	10
				C _L = 50 pF, V _{DD} = 5.0 V ± 10%, PAD3V5V = 0	—	—	20
				C _L = 100 pF, V _{DD} = 5.0 V ± 10%, PAD3V5V = 0	—	—	40
				C _L = 25 pF, V _{DD} = 3.3 V ± 10%, PAD3V5V = 1	—	—	12
				C _L = 50 pF, V _{DD} = 3.3 V ± 10%, PAD3V5V = 1	—	—	25
				C _L = 100 pF, V _{DD} = 3.3 V ± 10%, PAD3V5V = 1	—	—	40
W _{FRST}	SR	P	$\overline{\text{RESET}}$ input filtered pulse	—	—	40	ns
W _{NFRST}	SR	P	$\overline{\text{RESET}}$ input not filtered pulse	—	1000	—	ns
I _{WPU}	CC	P	Weak pull-up current absolute value	V _{DD} = 3.3 V ± 10%, PAD3V5V = 1	10	—	150
				V _{DD} = 5.0 V ± 10%, PAD3V5V = 0	10	—	150
				V _{DD} = 5.0 V ± 10%, PAD3V5V = 1 ⁴	10	—	250

¹ V_{DD} = 3.3 V ± 10% / 5.0 V ± 10%, T_A = –40 to 125 °C, unless otherwise specified

² This is a transient configuration during power-up, up to the end of reset PHASE2 (refer to the MC_RGM chapter of the *MPC5606BK Microcontroller Reference Manual*).

³ C_L includes device and package capacitance (C_{PKG} < 5 pF).

⁴ The configuration PAD3V5 = 1 when V_{DD} = 5 V is only transient configuration during power-up. All pads but RESET are configured in input or in high impedance state.

Table 31. ESD absolute maximum ratings^{1,2}

Symbol	Ratings	Conditions	Class	Max value ³	Unit
V _{ESD(HBM)}	Electrostatic discharge voltage (Human Body Model)	T _A = 25 °C conforming to AEC-Q100-002	H1C	2000	V
V _{ESD(MM)}	Electrostatic discharge voltage (Machine Model)	T _A = 25 °C conforming to AEC-Q100-003	M2	200	
V _{ESD(CDM)}	Electrostatic discharge voltage (Charged Device Model)	T _A = 25 °C conforming to AEC-Q100-011	C3A	500 750 (corners)	

¹ All ESD testing is in conformity with CDF-AEC-Q100 Stress Test Qualification for Automotive Grade Integrated Circuits.

² A device will be defined as a failure if after exposure to ESD pulses the device no longer meets the device specification requirements. Complete DC parametric and functional testing shall be performed per applicable device specification at room temperature followed by hot temperature, unless specified otherwise in the device specification.

³ Data based on characterization results, not tested in production

3.11.3.2 Static latch-up (LU)

Two complementary static tests are required on six parts to assess the latch-up performance:

- A supply overvoltage is applied to each power supply pin.
- A current injection is applied to each input, output and configurable I/O pin.

These tests are compliant with the EIA/JESD 78 IC latch-up standard.

Table 32. Latch-up results

Symbol	Parameter	Conditions	Class
LU	Static latch-up class	T _A = 125 °C conforming to JESD 78	II level A

3.12 Fast external crystal oscillator (4 to 16 MHz) electrical characteristics

The device provides an oscillator/resonator driver. [Figure 12](#) describes a simple model of the internal oscillator driver and provides an example of a connection for an oscillator or a resonator.

[Table 33](#) provides the parameter description of 4 MHz to 16 MHz crystals used for the design simulations.

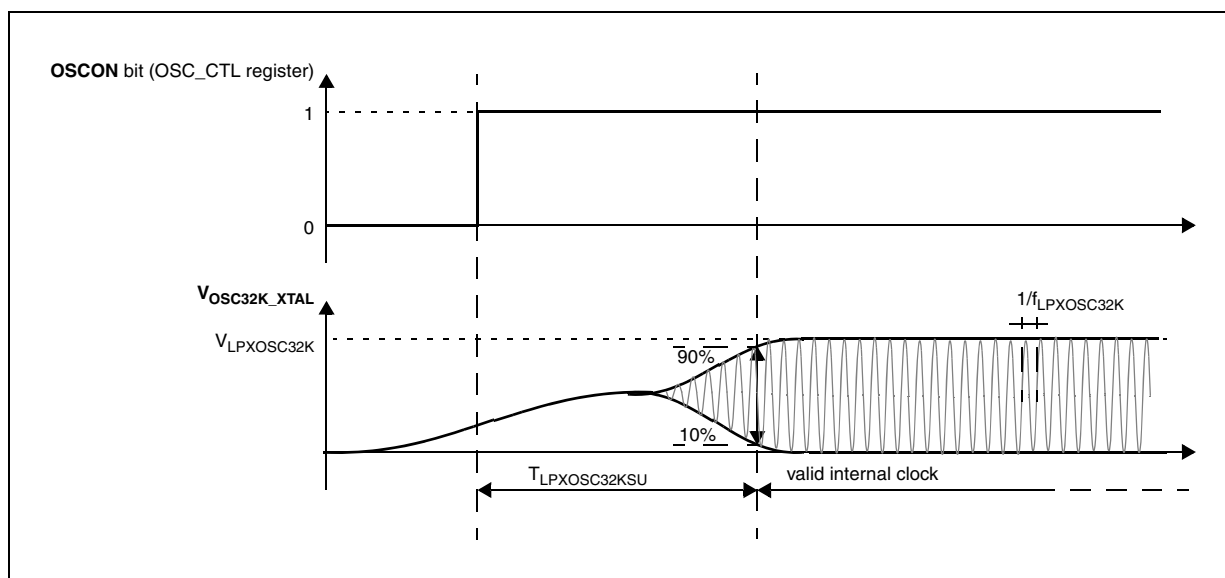


Figure 16. Slow external crystal oscillator (32 kHz) electrical characteristics

Table 36. Slow external crystal oscillator (32 kHz) electrical characteristics

Symbol	C	Parameter	Conditions ¹	Value			Unit
				Min	Typ	Max	
f_{SXOSC}	SR	—	Slow external crystal oscillator frequency	32	32.768	40	kHz
V_{SXOSC}	CC	T	Oscillation amplitude	—	2.1	—	V
$I_{SXOSCBIAS}$	CC	T	Oscillation bias current	—	2.5	—	μA
I_{SXOSC}	CC	T	Slow external crystal oscillator consumption	—	—	8	μA
$T_{SXOSCSU}$	CC	T	Slow external crystal oscillator start-up time	—	—	2 ²	s

¹ $V_{DD} = 3.3 V \pm 10\% / 5.0 V \pm 10\%$, $T_A = -40$ to $125^\circ C$, unless otherwise specified

² Start-up time has been measured with EPSON TOYOCOM MC306 crystal. Variation may be seen with other crystal.

3.14 FMPLL electrical characteristics

The device provides a frequency modulated phase locked loop (FMPLL) module to generate a fast system clock from the FXOSC or FIRC sources.

Table 37. FMPLL electrical characteristics

Symbol	C	Parameter	Conditions ¹	Value			Unit
				Min	Typ	Max	
f_{PLLIN}	SR	—	FMPLL reference clock ²	4	—	64	MHz
Δ_{PLLIN}	SR	—	FMPLL reference clock duty cycle ²	40	—	60	%

possible, ideally infinite. This capacitor contributes to attenuating the noise present on the input pin; furthermore, it sources charge during the sampling phase, when the analog signal source is a high-impedance source.

A real filter can typically be obtained by using a series resistance with a capacitor on the input pin (simple RC filter). The RC filtering may be limited according to the value of source impedance of the transducer or circuit supplying the analog signal to be measured. The filter at the input pins must be designed taking into account the dynamic characteristics of the input signal (bandwidth) and the equivalent input impedance of the ADC itself.

In fact a current sink contributor is represented by the charge sharing effects with the sampling capacitance: C_S being substantially a switched capacitance, with a frequency equal to the conversion rate of the ADC, it can be seen as a resistive path to ground. For instance, assuming a conversion rate of 1 MHz, with C_S equal to 3 pF, a resistance of 330 k Ω is obtained ($R_{EQ} = 1 / (f_c \times C_S)$, where f_c represents the conversion rate at the considered channel). To minimize the error induced by the voltage partitioning between this resistance (sampled voltage on C_S) and the sum of $R_S + R_F + R_L + R_{SW} + R_{AD}$, the external circuit must be designed to respect the [Equation 4](#):

Eqn. 4

$$V_A \cdot \frac{R_S + R_F + R_L + R_{SW} + R_{AD}}{R_{EQ}} < \frac{1}{2} \text{LSB}$$

[Equation 4](#) generates a constraint for external network design, in particular on resistive path. Internal switch resistances (R_{SW} and R_{AD}) can be neglected with respect to external resistances.

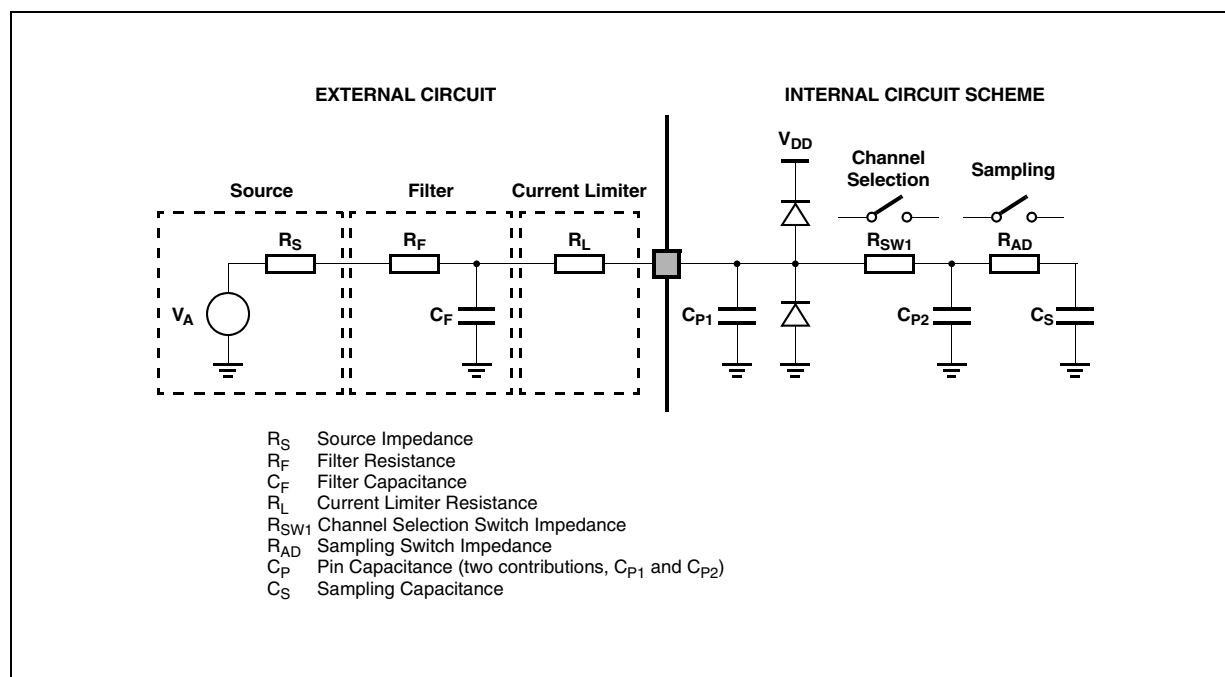


Figure 18. Input equivalent circuit (precise channels)

3.17.3 ADC electrical characteristics

Table 40. ADC input leakage current

Symbol	C	Parameter	Conditions	Value			Unit
				Min	Typ	Max	
I _{LKG}	CC	C	T _A = -40 °C	—	1	—	nA
			T _A = 25 °C		1	—	
			T _A = 85 °C		3	100	
			T _A = 105 °C		8	200	
			T _A = 125 °C		45	400	
			No current injection on adjacent pin		—	—	

Table 41. ADC_0 conversion characteristics (10-bit ADC_0)

Symbol	C	Parameter	Conditions ¹	Value			Unit
				Min	Typ	Max	
V _{SS_ADC0}	SR	—	Voltage on VSS_HV_ADC0 (ADC_0 reference) pin with respect to ground (V _{SS}) ²	—	—	0.1	V
V _{DD_ADC0}	SR	—	Voltage on VDD_HV_ADC pin (ADC reference) with respect to ground (V _{SS})	—	—	V _{DD} + 0.1	V
V _{AINx}	SR	—	Analog input voltage ³	V _{SS_ADC0} - 0.1	—	V _{DD_ADC0} + 0.1	V
I _{ADC0pwd}	SR	—	ADC_0 consumption in power down mode	—	—	50	μA
I _{ADC0run}	SR	—	ADC_0 consumption in running mode	—	—	5	mA
f _{ADC0}	SR	—	ADC_0 analog frequency	6	—	32 + 4%	MHz
Δ _{ADC0_SYS}	SR	—	ADC_0 digital clock duty cycle (ipg_clk)	45	—	55	%
t _{ADC0_PU}	SR	—	ADC_0 power up delay	—	—	1.5	μs
t _{ADC0_S}	CC	T	Sample time ⁵	0.5	—	—	μs
			f _{ADC} = 32 MHz, ADC0_conf_sample_input = 17	—	—	42	
t _{ADC0_C}	CC	P	Conversion time ⁶	0.625	—	—	μs
C _S	CC	D	ADC_0 input sampling capacitance	—	—	3	pF
C _{P1}	CC	D	ADC_0 input pin capacitance 1	—	—	3	pF
C _{P2}	CC	D	ADC_0 input pin capacitance 2	—	—	1	pF
C _{P3}	CC	D	ADC_0 input pin capacitance 3	—	—	1	pF

Table 41. ADC_0 conversion characteristics (10-bit ADC_0) (continued)

Symbol		C	Parameter	Conditions ¹		Value			Unit
						Min	Typ	Max	
R _{SW1}	CC	D	Internal resistance of analog source	—		—	—	3	kΩ
R _{SW2}	CC	D	Internal resistance of analog source	—		—	—	2	kΩ
R _{AD}	CC	D	Internal resistance of analog source	—		—	—	2	kΩ
I _{INJ}	SR	—	Input current Injection	Current injection on one ADC_0 input, different from the converted one	V _{DD} = 3.3 V ± 10%	−5	—	5	mA
					V _{DD} = 5.0 V ± 10%	−5	—	5	
INL	CC	T	Absolute value for integral nonlinearity	No overload		—	0.5	1.5	LSB
DNL	CC	T	Absolute differential nonlinearity	No overload		—	0.5	1.0	LSB
OFS	CC	T	Absolute offset error	—		—	0.5	—	LSB
GNE	CC	T	Absolute gain error	—		—	0.6	—	LSB
TUEP	CC	P	Total unadjusted error ⁷ for precise channels, input only pins	Without current injection		−2	0.6	2	LSB
		With current injection		−3	—	3			
TUEX	CC	T	Total unadjusted error ⁷ for extended channel	Without current injection		−3	1	3	LSB
		With current injection		−4		4			

¹ V_{DD} = 3.3 V ± 10% / 5.0 V ± 10%, T_A = –40 to 125 °C, unless otherwise specified.

² Analog and digital V_{SS} **must** be common (to be tied together externally).

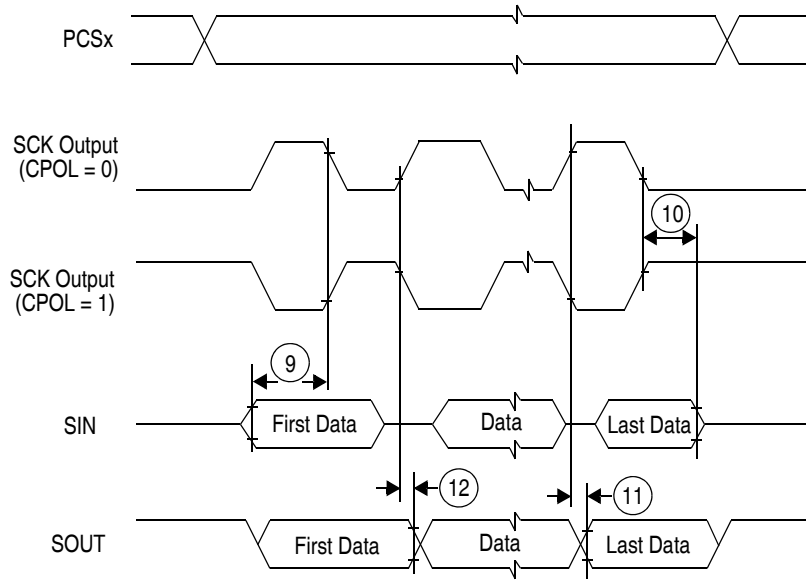
³ V_{AINx} may exceed V_{SS_ADC0} and V_{DD_ADC0} limits, remaining on absolute maximum ratings, but the results of the conversion will be clamped respectively to 0x000 or 0x3FF.

⁴ Duty cycle is ensured by using system clock without prescaling. When ADCLKSEL = 0, the duty cycle is ensured by internal divider by 2.

⁵ During the sample time the input capacitance C_S can be charged/discharged by the external source. The internal resistance of the analog source must allow the capacitance to reach its final voltage level within t_{ADC0_S}. After the end of the sample time t_{ADC0_S}, changes of the analog input voltage have no effect on the conversion result. Values for the sample clock t_{ADC0_S} depend on programming.

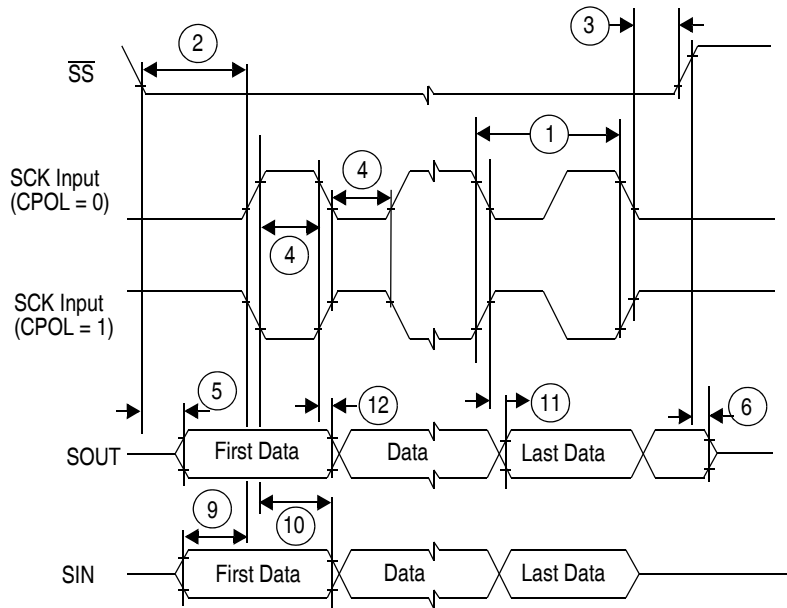
⁶ This parameter does not include the sample time t_{ADC0_S}, but only the time for determining the digital result and the time to load the result's register with the conversion result.

⁷ Total Unadjusted Error: The maximum error that occurs without adjusting Offset and Gain errors. This error is a combination of Offset, Gain and Integral Linearity errors.



Note: Numbers shown reference [Table 44](#).

Figure 24. DSPI classic SPI timing — master, CPHA = 1



Note: Numbers shown reference [Table 44](#).

Figure 25. DSPI classic SPI timing — slave, CPHA = 0

NOTES: 1. DIMENSIONS D1 AND E1 DO NOT INCLUDE MOLD PROTRUSION. ALLOWABLE PROTRUSION IS 0.25MM PER SIDE. DIMENSIONS D1 AND E1 DO INCLUDE MOLD MISMATCH AND ARE DETERMINED AT DATUM PLANE DATUM H. 2. DIMENSION b DOES NOT INCLUDE DAMBAR PROTRUSION. DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL NOT CAUSE THE LEAD WIDTH TO EXCEED THE MAXIMUM b DIMENSION BY MORE THEN 0.08MM. DAMBAR CAN NOT BE LOCATED ON THE LOWER RADIUS OR THE FOOT. MINIMUM BETWEEN PROTRUSION AND AN ADJACENT LEAD IS 0.07MM FOR 0.4MM AND 0.5MM PITCH PACKAGES.											
DIM	MIN	NOM	MAX	DIM	MIN	NOM	MAX	DIM	MIN	NOM	MAX
A	---		1.6	L1		1 REF					
A1	0.05		0.15	R1	0.08		---				
A2	1.35	1.4	1.45	R2	0.08		0.2				
b	0.17	0.22	0.27	S		0.2 REF					
b1	0.17	0.2	0.23	Ø	0°	3.5°	7°				
c	0.09		0.2	Ø1	0°		---				
c1	0.09		0.16	Ø2	11°	12°	13°				
D		26 BSC		Ø3	11°	12°	13°				
D1		24 BSC									
e		0.5 BSC									
E		26 BSC									
E1		24 BSC									
L	0.45	0.6	0.75		UNIT	DIMENSION AND TOLERANCES		REFERENCE DOCUMENT			
					MM	ASME Y14.5M		64-06-280-1392			

Figure 35. 176 LQFP package mechanical drawing (Part 3 of 3)

6 Revision history

Table 46. Revision history

Revision	Date	Description of changes
1	22 Apr 2011	Initial release.
2	15 May 2013	Changed device number to MPC5606BK. In Table 2 (Functional port pins), updated PA[11] AF2, PD[13] AF2, and PH[11] AF3 I/O direction to "I/O". In Table 3 (Pad types), corrected "Fast" in the "S" row to "Slow." In Table 5 (PAD3V5V field description), updated footnote 2. In Table 6 (OSCILLATOR_MARGIN field description), updated footnote 2. Inserted Section 3.2.3, NVUSRO[WATCHDOG_EN] field description. In Table 8 (Absolute maximum ratings), Table 9 (Recommended operating conditions (3.3 V)), and Table 10 (Recommended operating conditions (5.0 V)), corrected the parameter description for V_{DD_ADC} to "Voltage on VDD_HV_ADC0, VDD_HV_ADC1 (ADC reference) with respect to ground (V_{SS})" In Section 3.6.1, I/O pad types bullet item, removed Nexus reference. In Table 12 (I/O input DC electrical characteristics), added specifications for 85 °C. In Table 13 (I/O pull-up/pull-down DC electrical characteristics), Table 14 (SLOW configuration output buffer electrical characteristics), Table 15 (MEDIUM configuration output buffer electrical characteristics), and Table 16 (FAST configuration output buffer electrical characteristics), changed sentence in footnote 2 to "All pads but RESET are configured in input or in high impedance state." In Table 15 (MEDIUM configuration output buffer electrical characteristics), for V_{OL}, changed I_{OH} to I_{OL}. Updated Table 20 (I/O weight). In Table 21 (Reset electrical characteristics) changed sentence in footnote 4 to "All pads but RESET are configured in input or in high impedance state." In Table 22 (Voltage regulator electrical characteristics), corrected the maximum value for I_{DD_BV} in Table 22 (Voltage regulator electrical characteristics) to 300 mA. In Table 23 (Low voltage monitor electrical characteristics), changed V_{PORUP} classification tag from "P" (Production testing guaranteed) to "D" (Design simulation). Changed $V_{LVDHV3BH}$ classification tag from "P" (Production testing guaranteed) to "T" (Design characterization). In Table 23 (Low voltage monitor electrical characteristics), changed $V_{LVDHV3L}$, $V_{LVDHV3BL}$ minimums from 2.7 V to 2.6 V.

Table 46. Revision history (continued)

Revision	Date	Description of changes
2 (cont.)	15 May 2013	In Table 24 (Electrical characteristics in different application modes), — Changed I_{DDMAX} Typ to 81 mA and I_{DDMAX} Typ to 130 mA. — Changed I_{DDRUN} Typ for fCPU = 32 MHz to 40 mA. — Changed I_{DDRUN} Typ for fCPU = 48 MHz to 54 mA. Added I_{DDRUN} Max of 96 mA. — Changed I_{DDRUN} Typ for fCPU = 64 MHz to 67 mA. Added I_{DDRUN} Max of 120 mA. — Changed I_{DDHALT} at $T_A = 25\text{ °C}$ Typ to 10 mA and I_{DDHALT} Max to 15 mA. — Changed I_{DDHALT} at $T_A = 125\text{ °C}$ Typ to 15 mA and I_{DDHALT} Max to 28 mA. — Changed I_{DDSTOP} T_A temperature from -40 °C to 25 °C. — Changed I_{DDSTOP} at $T_A = 25\text{ °C}$ Typ to 130 μA and I_{DDSTOP} Max to 500 μA. — Changed I_{DDSTOP} at $T_A = 55\text{ °C}$ Typ to 180 μA. — Changed I_{DDSTOP} at $T_A = 85\text{ °C}$ Typ to 1 mA and I_{DDSTOP} Max to 5 mA. — Changed I_{DDSTOP} at $T_A = 105\text{ °C}$ Typ to 3 mA and I_{DDSTOP} Max to 9 mA. — Changed I_{DDSTOP} at $T_A = 125\text{ °C}$ Typ to 5 mA and I_{DDSTOP} Max to 14 mA. — Changed $I_{DDSTDBY2}$ at $T_A = 25\text{ °C}$ Typ to 17 μA and Max to 80 μA. — Changed $I_{DDSTDBY2}$ at $T_A = 55\text{ °C}$ Typ to 30 μA. — Changed $I_{DDSTDBY2}$ at $T_A = 85\text{ °C}$ Typ to 100 μA. — Changed $I_{DDSTDBY2}$ at $T_A = 105\text{ °C}$ Typ to 280 μA and Max to 950 μA. — Changed $I_{DDSTDBY2}$ at $T_A = 125\text{ °C}$ Typ to 460 μA and Max to 1700 μA. — Changed the parameter classification for $I_{DDSTANDBY2}$ ($T_A = 125\text{ °C}$) — Changed $I_{DDSTDBY1}$ at $T_A = 25\text{ °C}$ Typ to 12 μA and Max to 50 μA. — Changed $I_{DDSTDBY1}$ at $T_A = 55\text{ °C}$ Typ to 24 μA. — Changed $I_{DDSTDBY1}$ at $T_A = 85\text{ °C}$ Typ to 48 μA. — Changed $I_{DDSTDBY1}$ at $T_A = 105\text{ °C}$ Typ to 150 μA and Max to 500 μA. — Changed $I_{DDSTDBY1}$ at $T_A = 125\text{ °C}$ Typ to 260 μA. — Changed the third sentence of Footnote 3 to begin with “The given value is thought to be a worst case value (64 MHz at 125 °C) with all peripherals running.” — Removed footnotes 8 and 9 regarding I_{DDHALT} and I_{DDSTOP} — Corrected “C” characteristics to reflect testing status. In Section 3.10, Flash memory electrical characteristics, removed the “FLASH_BIU settings vs. frequency of operation” table. In Table 28 (Flash power supply DC electrical characteristics), corrected Footnote 2 to specify 125 °C. In Section 3.14, FMPLL electrical characteristics, changed the text “the main oscillator driver” to “the FXOSC or FIRC sources.” In Table 40 (ADC input leakage current), added specifications for 85 °C. In Table 44 (DSPI characteristics), added t_{SCK} specifications for MTFE=1. In Table 44 (DSPI characteristics), updated specifications 7 and 8 to 13 ns, all DSPIs. In ADC section, corrected Equation 11. In Figure 41 (Commercial product code structure), added “Note: Not all options are available on all devices.” Removed Section 6, Abbreviations.
3	11 Sep 2013	Updated the temperature in table note 2 in Table 1 (MPC5606BK family comparison) from 105 °C to 125 °C .
4	25 Nov 2015	Updated the Max value current for $I_{ADC0run}$ from 40 mA to 5 mA in Table 41 (ADC_0 conversion characteristics (10-bit ADC_0)) .
5	7 Nov 2017	In Table 9 (Recommended operating conditions (3.3 V)) added Min value for TV_{DD}. In Table 10 (Recommended operating conditions (5.0 V)) added Min value for TV_{DD}. In Table 44 (DSPI characteristics) changed the for DSPI 2 and 4, in MTFE=1 mode from 125 to 145.